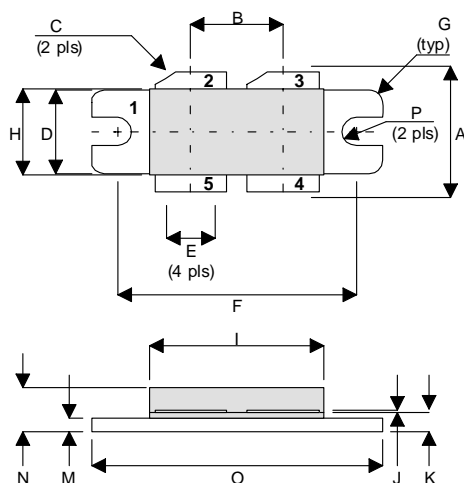


**MECHANICAL DATA**



**D1**

PIN 1	SOURCE (COMMON)	PIN 2	DRAIN 1
PIN 3	DRAIN 2	PIN 4	GATE 2
PIN 5	GATE 1		

DIM	Millimetres	Tol.	Inches	Tol.
A	15.24	0.50	0.600	0.020
B	10.80	0.13	0.425	0.005
C	45°	5°	45°	5°
D	9.78	0.13	0.385	0.005
E	8.38	0.13	0.330	0.005
F	27.94	0.13	1.100	0.005
G	1.52R	0.13	0.060R	0.005
H	10.16	0.15	0.400	0.006
I	21.84	0.23	0.860	0.009
J	0.10	0.02	0.004	0.001
K	1.96	0.13	0.077	0.005
M	1.02	0.13	0.040	0.005
N	4.45	0.38	0.175	0.015
O	34.04	0.13	1.340	0.005
P	1.63R	0.13	0.064R	0.005

**GOLD METALLISED**  
**MULTI-PURPOSE SILICON**  
**DMOS RF FET**  
**350W – 50V – 175MHz**  
**PUSH-PULL**

**FEATURES**

- SUITABLE FOR BROAD BAND APPLICATIONS
- SIMPLE BIAS CIRCUITS
- ULTRA-LOW THERMAL RESISTANCE
- BeO FREE
- LOW Crss
- HIGH GAIN – 20 dB MINIMUM

**APPLICATIONS**

- VHF/UHF COMMUNICATIONS  
from 1 MHz to 400 MHz

**ABSOLUTE MAXIMUM RATINGS** ( $T_{case} = 25^{\circ}C$  unless otherwise stated)

$P_D$	Power Dissipation	875W (438W -A Version)
$BV_{DSS}$	Drain – Source Breakdown Voltage *	125V
$BV_{GSS}$	Gate – Source Breakdown Voltage*	±20V
$I_{D(sat)}$	Drain Current*	21A
$T_{stg}$	Storage Temperature	-65 to 150°C
$T_j$	Maximum Operating Junction Temperature	200°C

\* Per Side

Semelab Plc reserves the right to change test conditions, parameter limits and package dimensions without notice. Information furnished by Semelab is believed to be both accurate and reliable at the time of going to press. However Semelab assumes no responsibility for any errors or omissions discovered in its use. Semelab encourages customers to verify that datasheets are current before placing orders.

### ELECTRICAL CHARACTERISTICS (T<sub>case</sub> = 25°C unless otherwise stated)

Parameter	Test Conditions	Min.	Typ.	Max.	Unit
<b>PER SIDE</b>					
B <sub>V</sub> DSS	Drain-Source Breakdown Voltage V <sub>GS</sub> = 0 I <sub>D</sub> = 100mA	125			V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current V <sub>DS</sub> = 50V V <sub>GS</sub> = 0			7	mA
I <sub>GSS</sub>	Gate Leakage Current V <sub>GS</sub> = 20V V <sub>DS</sub> = 0			1	μA
V <sub>GS(th)</sub>	Gate Threshold Voltage* I <sub>D</sub> = 10mA V <sub>DS</sub> = V <sub>GS</sub>	1		7	V
g <sub>fs</sub>	Forward Transconductance* V <sub>DS</sub> = 10V I <sub>D</sub> = 3.5A	5.6			mhos
V <sub>GS(th)match</sub>	Gate Threshold Voltage Matching Between Sides I <sub>D</sub> = 10mA V <sub>DS</sub> = V <sub>GS</sub>			0.1	V
<b>TOTAL DEVICE</b>					
G <sub>PS</sub>	Common Source Power Gain P <sub>O</sub> = 350W	20			dB
η	Drain Efficiency V <sub>DS</sub> = 50V I <sub>DQ</sub> = 1.4A	60			%
VSWR	Load Mismatch Tolerance f = 175MHz	20:1			—
<b>PER SIDE</b>					
C <sub>iss</sub>	Input Capacitance V <sub>DS</sub> = 50V V <sub>GS</sub> = -5V f = 1MHz			420	pF
C <sub>oss</sub>	Output Capacitance V <sub>DS</sub> = 50V V <sub>GS</sub> = 0 f = 1MHz			175	pF
C <sub>rss</sub>	Reverse Transfer Capacitance V <sub>DS</sub> = 50V V <sub>GS</sub> = 0 f = 1MHz			10.5	pF

\* Pulse Test: Pulse Duration = 300 μs , Duty Cycle ≤ 2%

### THERMAL DATA

R <sub>THj-case</sub>	Thermal Resistance Junction – Case	Max. 0.2°C / W 0.4 °C / W -A Version
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